

#### 1. Global joint venture starts operations as WeEn Semiconductors

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As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



Product data sheet

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT404 (D2PAK) surface mountable plastic package. This "series E" triac balances the requirements of commutation performance and gate sensitivity. The "sensitive gate" "series E" is intended for interfacing with low power drivers including microcontrollers.

#### 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Sensitive gate for easy logic level triggering
- Surface mountable package
- · Triggering in three quadrants only

### 3. Applications

- Electronic thermostats (heating and cooling)
- High power motor controls e.g. washing machines and vacuum cleaners

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage			-	-	800	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5		-	-	100	Α
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 100 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3		-	-	12	Α
Static characte	Static characteristics						
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$		2	-	10	mA





Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	10	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	2	-	10	mA

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2		sym051
3	G	gate		·
mb	T2	mounting base; main terminal 2	1 3	
			D2PAK (SOT404)	

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BTA312B-800E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404			

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 100 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	12	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 20  \text{ms}$ ; Fig. 4; Fig. 5	-	100	А
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 16.7  \text{ms}$	-	110	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	50	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
T <sub>j</sub>	junction temperature		-	125	°C

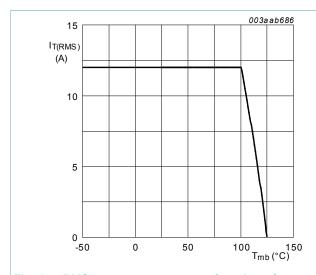
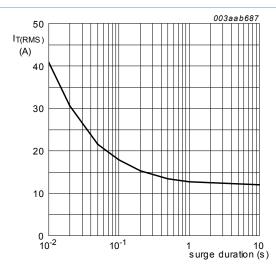


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values

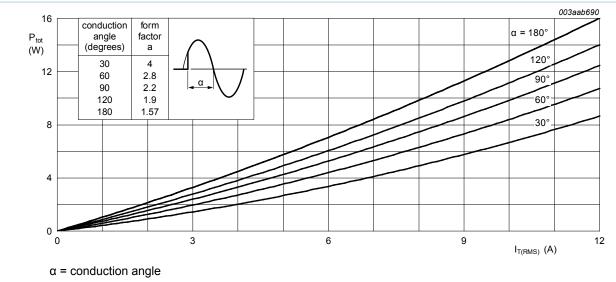


 $f = 50 \text{ Hz}; T_{mb} = 100 \text{ }^{\circ}\text{C}$ 

Fig. 2. RMS on-state current as a function of surge duration; maximum values

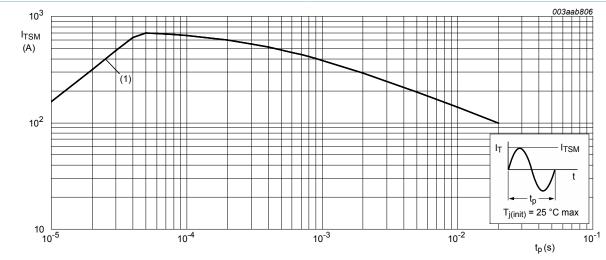
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**3Q Hi-Com Triac** 



a = form factor =  $I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



 $t_p \le 20 \text{ ms}$ 

(1) dl<sub>T</sub>/dt limit

Fig. 4. Non-repetitive peak on-state current as a function of pulse duration; maximum values

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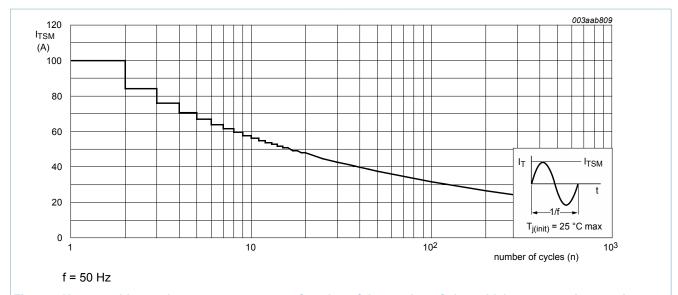


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

### 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; Fig. 6	-	-	1.5	K/W
		half cycle; Fig. 6	-	-	2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	printed circuit board mounted; minimum footprint	-	55	-	K/W

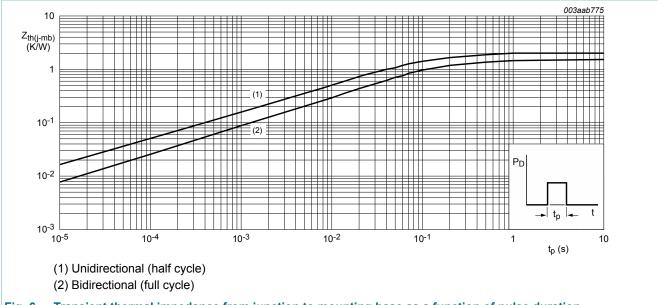
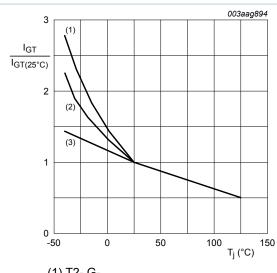


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 7$	2	-	10	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 7}}$	2	-	10	mA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	25	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	30	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; } T2\text{- }G\text{-;}$ $T_j = 25 \text{ °C; } \underline{\text{Fig. 8}}$	-	-	35	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	15	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	0.8	1	V
		V <sub>D</sub> = 400 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.25	0.4	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic cl	naracteristics				'	,
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	50	-	-	V/µs
dI <sub>com</sub> /dt	rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit	3	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit	6	-	-	A/ms
		$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 1 V/ $\mu$ s; gate open circuit	10	-	-	A/ms



- (1) T2- G-
- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

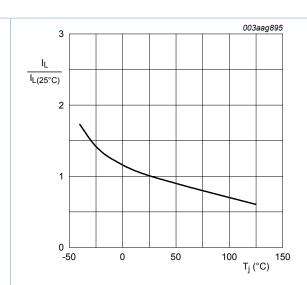


Fig. 8. Normalized latching current as a function of junction temperature

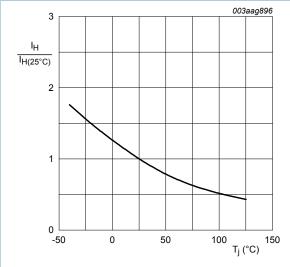
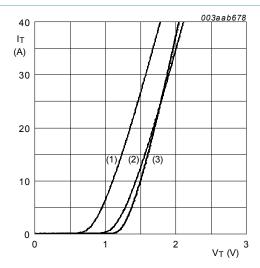


Fig. 9. Normalized holding current as a function of junction temperature



 $V_o$  = 1.164 V;  $R_s$  = 0.027  $\Omega$ 

(1) T<sub>j</sub> = 125 °C; typical values

(2) T<sub>i</sub> = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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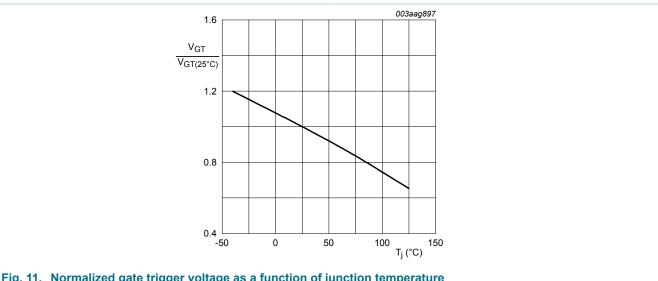
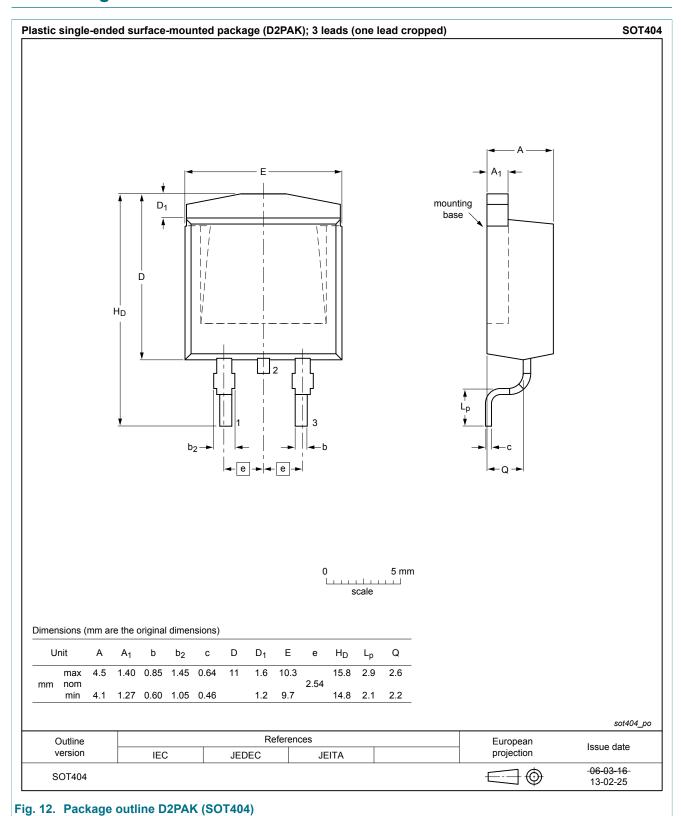


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

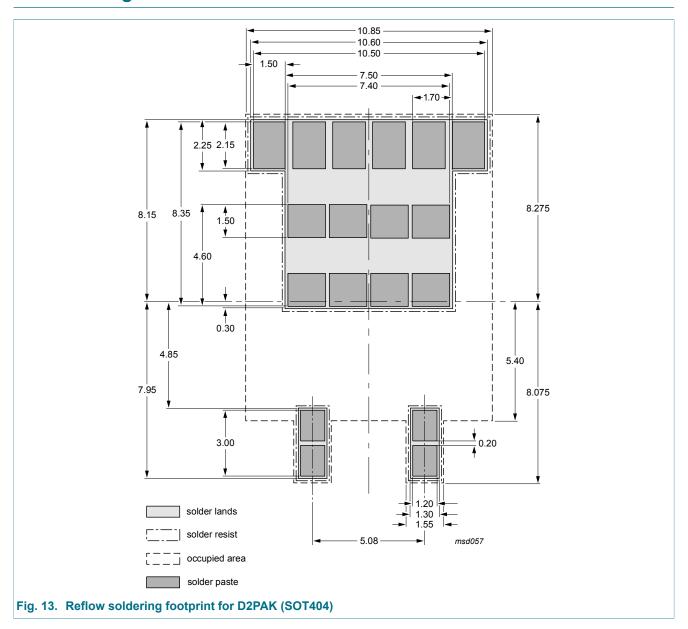
## 10. Package outline



**Product data sheet** 

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# 11. Soldering



#### 12. Legal information

#### 12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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